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(54) **RESIST COMPOSITION AND PATTERNING PROCESS**

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See application file for complete search history.

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(57) **ABSTRACT**

To a resist composition comprising a polymer comprising recurring units having an acid labile group and an acid generator is added a metal-acid complex. The metal is Ce, Cu, Zn, Fe, In, Y, Yb, Sn, Tm, Sc, Ni, Nd, Hf, Zr, Ti, La, Ag, Ba, Ho, Tb, Lu, Eu, Dy, Gd, Rb, Sr or Cs. The acid is a fluoroalkylsulfonic acid, fluorinated arylsulfonic acid, fluorinated tetraphenylboric acid, fluoroalkylsulfonimide acid or fluoroalkylsulfonemethide acid. Due to a high contrast of alkaline dissolution rate before and after exposure, high resolution, high sensitivity, and controlled acid diffusion rate, the composition forms a pattern with satisfactory profile and minimal line edge roughness.

14 Claims, No Drawings